(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
23 February 2012 (23.02.2012)

PCT

(10) International Publication Number
WO 2012/024056 A2

(51) International Patent Classification:
H01L 21/28 (2006.01) *H01L 21/203* (2006.01)

(21) International Application Number:
PCT/US2011/045067

(22) International Filing Date:
22 July 2011 (22.07.2011)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
12/860,745 20 August 2010 (20.08.2010) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *without international search report and to be republished upon receipt of that report (Rule 48.2(g))*

(54) **Title**: SEMICONDUCTOR CONSTRUCTIONS; AND METHODS FOR PROVIDING ELECTRICALLY CONDUCTIVE MATERIAL WITHIN OPENINGS

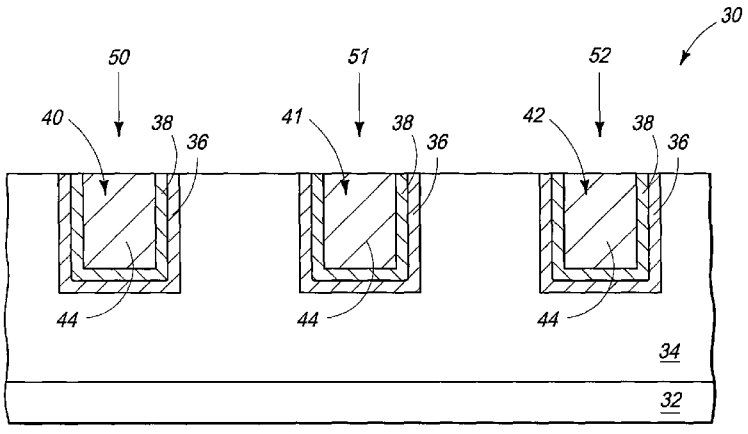


Fig. 8

(57) **Abstract**: Some embodiments include methods for depositing copper-containing material utilizing physical vapor deposition of the copper-containing material while keeping a temperature of the deposited copper-containing material at greater than 100°C. Some embodiments include methods in which openings are lined with a metal-containing composition, copper-containing material is physical vapor deposited over the metal- containing composition while a temperature of the copper-containing material is no greater than about 0°C, and the copper-containing material is then annealed while the copper-containing material is at a temperature in a range of from about 180°C to about 250°C. Some embodiments include methods in which openings are lined with a composition containing metal and nitrogen, and the lined openings are at least partially filled with copper-containing material. Some embodiments include semiconductor constructions having a metal nitride liner along sidewall peripheries of an opening, and having copper-containing material within the opening and directly against the metal nitride liner.

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